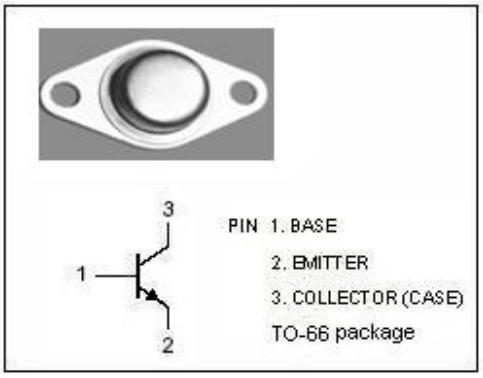
isc Silicon PNP Power Transistor 2N3741A



DESCRIPTION

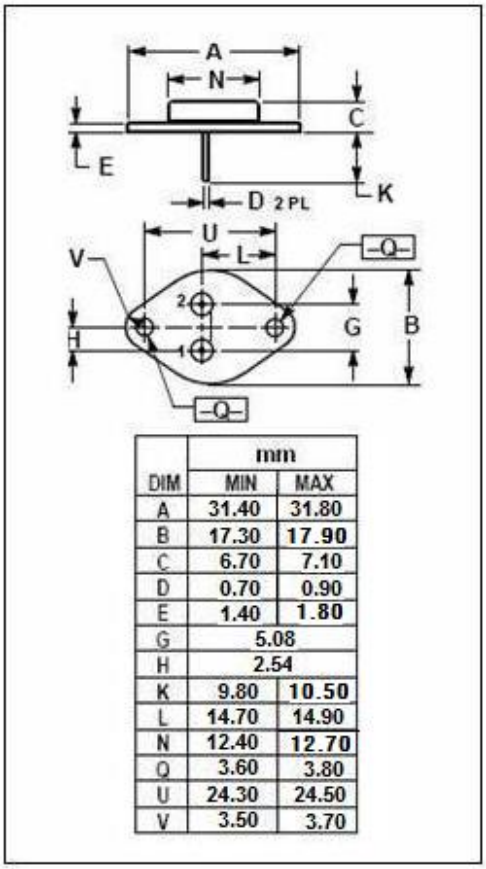
- Collector-Emitter Breakdown Voltage-
  : V_{CEO}=-80V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

APPLICATIONS

- Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-4	A
P_D	Collector Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	-65~200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C=-100mA	-80			V
I_{CBO}	Collector-Base Cutoff Current	V_{CB}=- 80V			-0.1	uA
I_{CEO}	Collector-Emitter Cutoff Current	V_{CE}= -60V			-1	uA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B=-0.125A			-0.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C=-0.25A; V_{CE}= -1V			-1	V
h_{FE-1}	DC Current Gain	I_C=-100mA; V_{CE}=-1V	40			
h_{FE-2}	DC Current Gain	I_C=-250mA; V_{CE}= -1V	30		100	
h_{FE-3}	DC Current Gain	I_C=-500mA; V_{CE}= -1V	20			
h_{FE-4}	DC Current Gain	I_C=-1A; V_{CE}= -1V	10			